

BAS21W series

High-voltage switching diodes

Rev. 01 — 9 October 2009

Product data sheet

1. Product profile

1.1 General description

High-voltage switching diodes, encapsulated in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Configuration	Package		Package configuration
		NXP	JEDEC	
BAS21W	single	SOT323	SC-70	very small
BAS21AW	dual common anode			
BAS21SW	dual series			

1.2 Features

- High switching speed: $t_{rr} \leq 50$ ns
- Low leakage current
- High reverse voltage: $V_R \leq 250$ V
- Low capacitance: $C_d \leq 2$ pF
- Very small SMD plastic package
- AEC-Q101 qualified

1.3 Applications

- High-speed switching
- General-purpose switching
- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
I_F	forward current		[1] -	-	225	mA
I_R	reverse current	$V_R = 200$ V	-	-	100	nA
V_R	reverse voltage		-	-	250	V
t_{rr}	reverse recovery time		[2] -	-	50	ns

[1] Single diode loaded.

[2] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA.

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
BAS21W			
1	anode		 006aaa764
2	not connected		
3	cathode		
BAS21AW			
1	cathode (diode 1)		 006aab099
2	cathode (diode 2)		
3	common anode		
BAS21SW			
1	anode (diode 1)		 006aaa763
2	cathode (diode 2)		
3	cathode (diode 1), anode (diode 2)		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
BAS21W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BAS21AW			
BAS21SW			

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BAS21W	X4*
BAS21AW	X6*
BAS21SW	X5*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per diode						
V_R	reverse voltage		-	250	V	
I_F	forward current		^[1] -	225	mA	
			^[2] -	125	mA	
I_{FRM}	repetitive peak forward current		-	625	mA	
I_{FSM}	non-repetitive peak forward current	square wave	^[3]			
		$t_p = 1 \mu s$		-	9	A
		$t_p = 100 \mu s$		-	3	A
		$t_p = 10 ms$		-	1.7	A
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C}$	^[4] -	200	mW	
T_j	junction temperature		-	150	$^\circ\text{C}$	
T_{amb}	ambient temperature		-55	+150	$^\circ\text{C}$	
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$	

[1] Single diode loaded.

[2] Double diode loaded.

[3] $T_j = 25 \text{ }^\circ\text{C}$ prior to surge.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	300	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

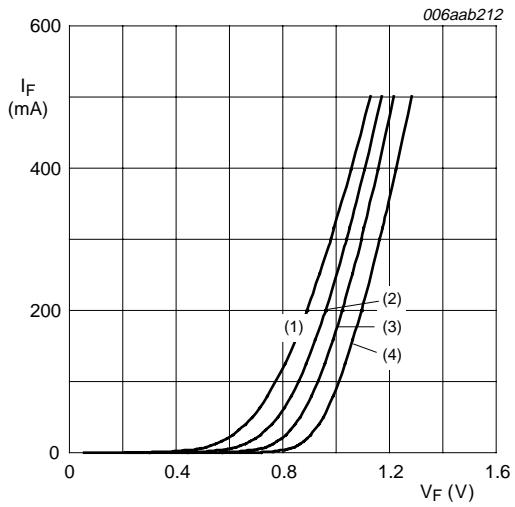
7. Characteristics

Table 8. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

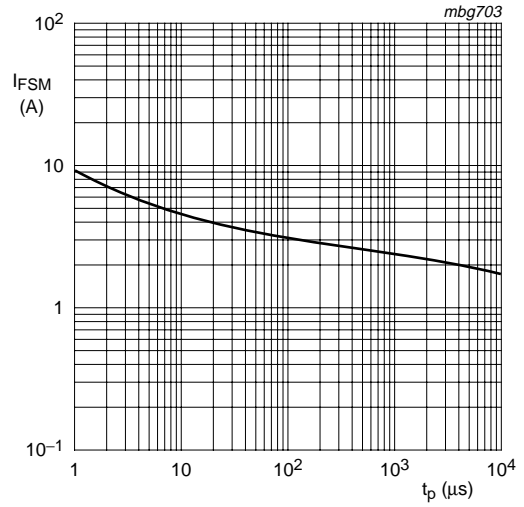
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_F	forward voltage	$I_F = 100\text{ mA}$	-	-	1.0	V
		$I_F = 200\text{ mA}$	-	-	1.25	V
I_R	reverse current	$V_R = 200\text{ V}$	-	-	100	nA
		$V_R = 200\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	100	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0\text{ V}$	-	-	2	pF
t_{rr}	reverse recovery time		[1]	-	50	ns

[1] When switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$.



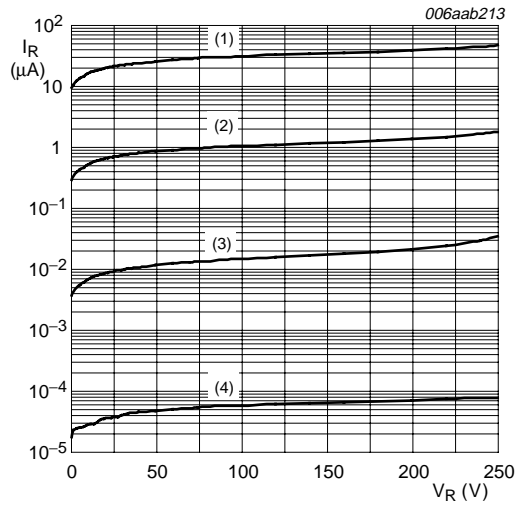
- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$
- (4) $T_{amb} = -40\text{ °C}$

Fig 1. Forward current as a function of forward voltage; typical values



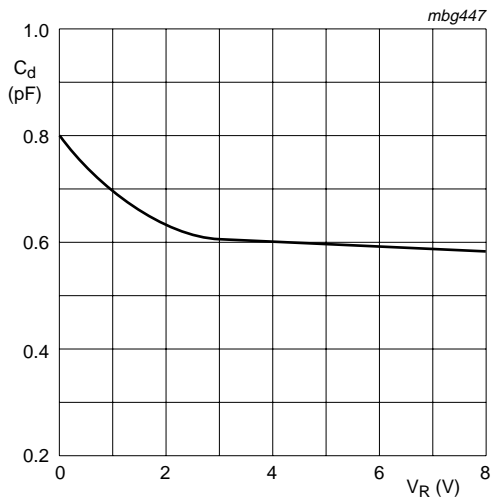
Based on square wave currents.
 $T_j = 25\text{ °C}$; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



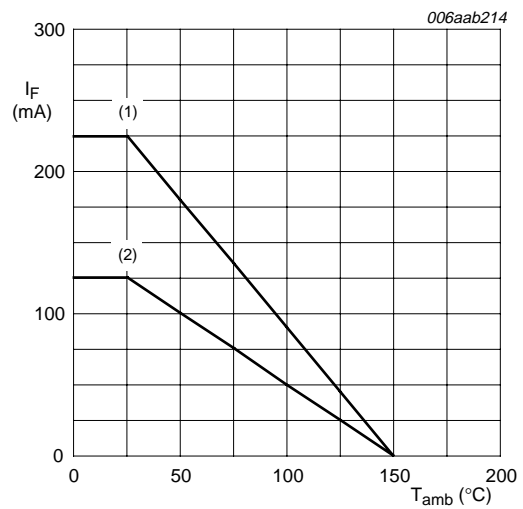
- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$
- (4) $T_{amb} = -40\text{ °C}$

Fig 3. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 4. Diode capacitance as a function of reverse voltage; typical values

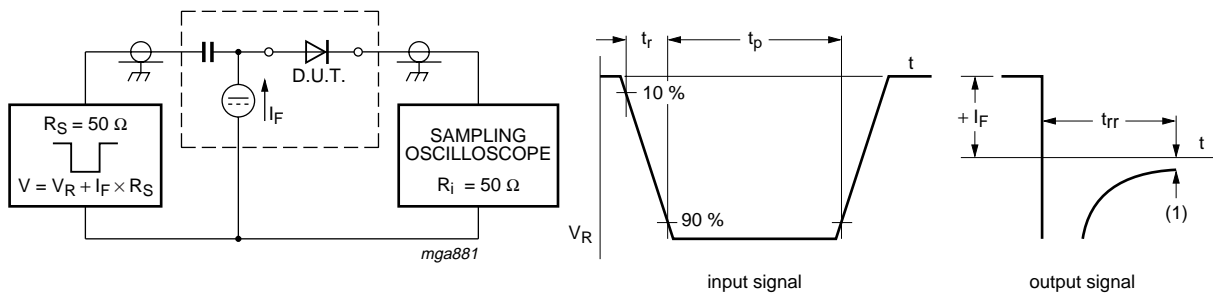


FR4 PCB, standard footprint

- (1) Single diode loaded.
- (2) Double diode loaded.

Fig 5. Forward current as a function of ambient temperature; derating curve

8. Test information



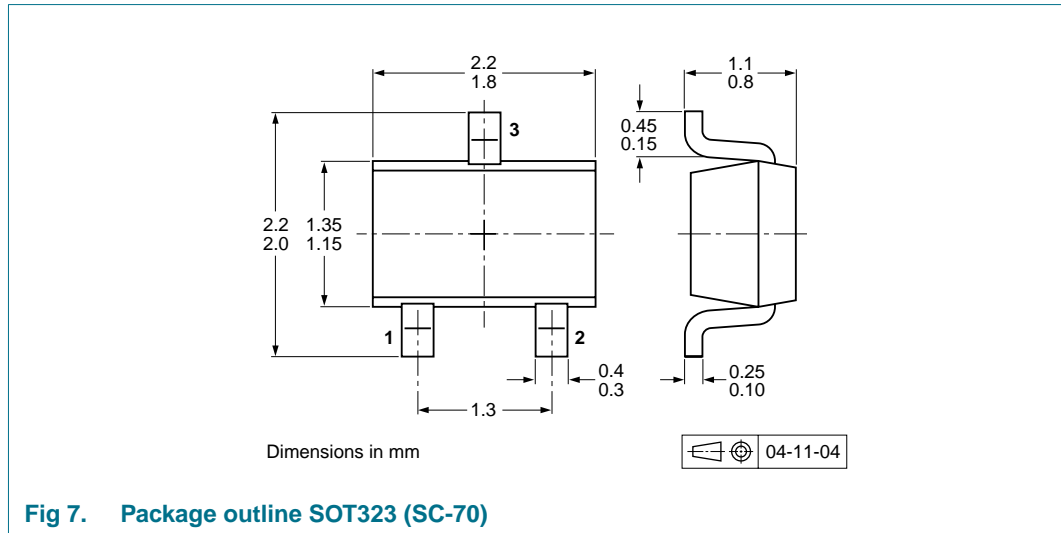
(1) I_R = 1 mA

Fig 6. Reverse recovery time test circuit and waveforms

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAS21W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135
BAS21AW				
BAS21SW				

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

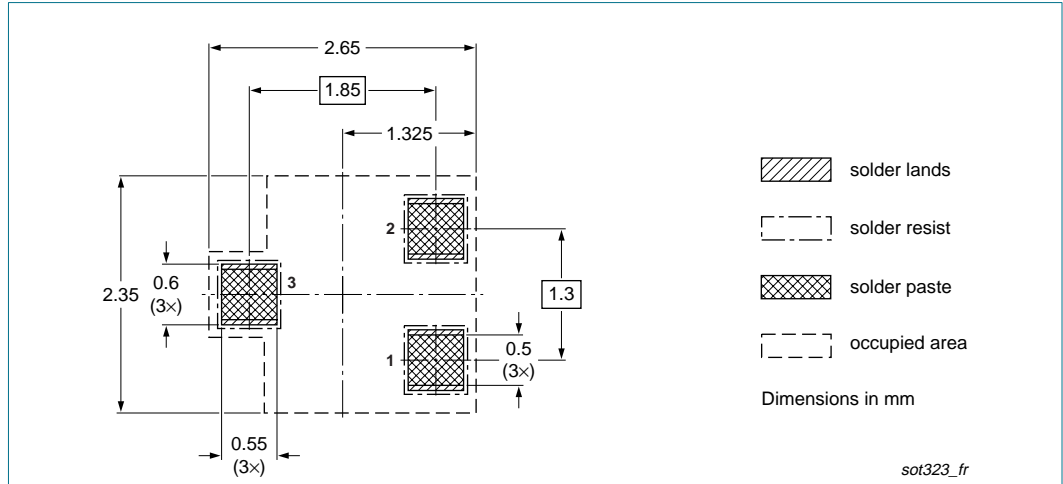


Fig 8. Reflow soldering footprint SOT323 (SC-70)

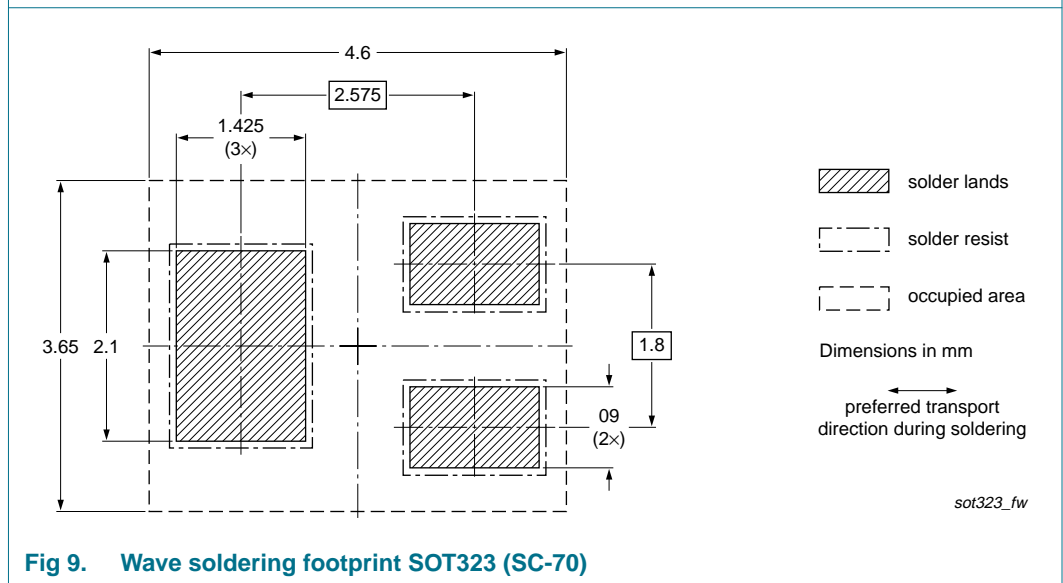


Fig 9. Wave soldering footprint SOT323 (SC-70)

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS21W_SER_1	20091009	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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